

Single P-channel MOSFET

ELM34403AA-N

■General description

ELM34403AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

■Features

- $V_{ds} = -55V$
- $I_d = -4.5A$
- $R_{ds(on)} < 80m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} < 150m\Omega$ ($V_{gs} = -4.5V$)

■Maximum absolute ratings

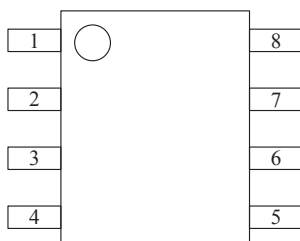
Parameter		Symbol	Limit	Unit	Note
Drain-source voltage		V_{ds}	-55	V	
Gate-source voltage		V_{gs}	± 20	V	
Continuous drain current	$T_a = 25^\circ C$	I_d	-4.5	A	
	$T_a = 70^\circ C$		-3.5		
Pulsed drain current		I_{dm}	-20	A	3
Power dissipation	$T_a = 25^\circ C$	P_d	2.5	W	
	$T_a = 70^\circ C$		1.3		
Junction and storage temperature range		T_j, T_{stg}	-55 to 150	$^\circ C$	

■Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	Steady-state	$R_{\theta ja}$		50	$^\circ C/W$	

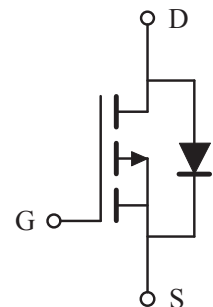
■Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■Circuit



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■Electrical characteristics

Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BVdss	Id=-250μA, Vgs=0V	-55			V	
Zero gate voltage drain current	Idss	Vds=-44V, Vgs=0V			-1	μA	
		Vds=-36V,Vgs=0V,Tj=125°C			-10		
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V			±250	nA	
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=-250μA	-1.0	-1.5	-2.5	V	
On state drain current	Id(on)	Vgs=-10V, Vds=-5V	-20			A	1
Static drain-source on-resistance	Rds(on)	Vgs=-10V, Id=-4.5A		60	80	mΩ	1
		Vgs=-4.5V, Id=-3.5A		90	150	mΩ	
Forward transconductance	Gfs	Vds=-10V, Id=-4.5A		9		S	1
Diode forward voltage	Vsd	Is=If, Vgs=0V			-1	V	1
Max. body-diode continuous current	Is				-1.3	A	
Pulsed body-diode current	Ism				-2.6	A	3
DYNAMIC PARAMETERS							
Input capacitance	Ciss	Vgs=0V, Vds=-30V, f=1MHz		760		pF	
Output capacitance	Coss			90		pF	
Reverse transfer capacitance	Crss			40		pF	
SWITCHING PARAMETERS							
Total gate charge	Qg	Vgs=-10V, Vds=-27.5V Id=-4.5A		15.0		nC	2
Gate-source charge	Qgs			2.5		nC	2
Gate-drain charge	Qgd			3.0		nC	2
Turn-on delay time	td(on)	Vgs=-10V, Vds=-20V Id≈-1A, Rgen=6Ω		7	14	ns	2
Turn-on rise time	tr			10	20	ns	2
Turn-off delay time	td(off)			19	34	ns	2
Turn-off fall time	tf			12	22	ns	2
Body diode reverse recovery time	trr	If=-3.5A, dl/dt=100A/μs		15.5		ns	
Body diode reverse recovery charge	Qrr	If=-3.5A, dl/dt=100A/μs		7.9		nC	

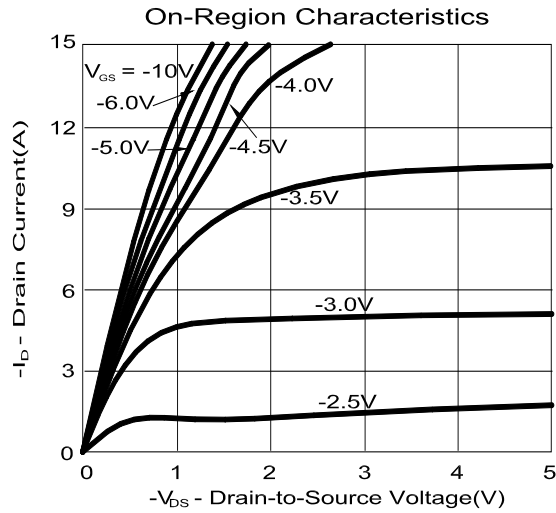
NOTE :

1. Pulsed width≤300μsec and Duty cycle≤2%.
2. Independent of operating temperature.
3. Pulsed width limited by maximum junction temperature.
4. Duty cycle ≤ 1%.

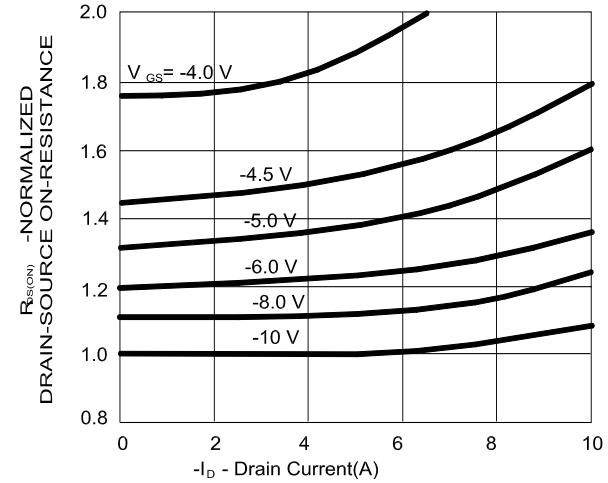
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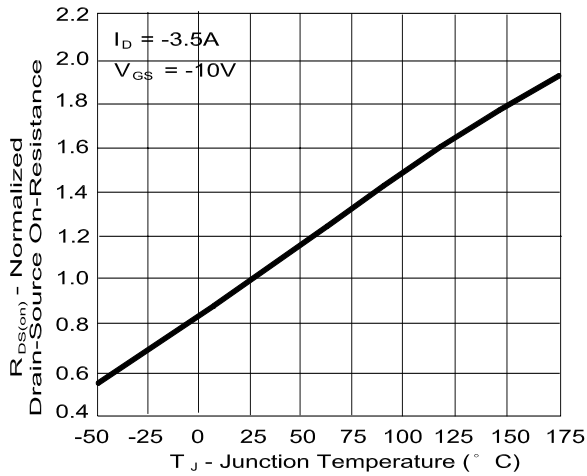
■ Typical electrical and thermal characteristics



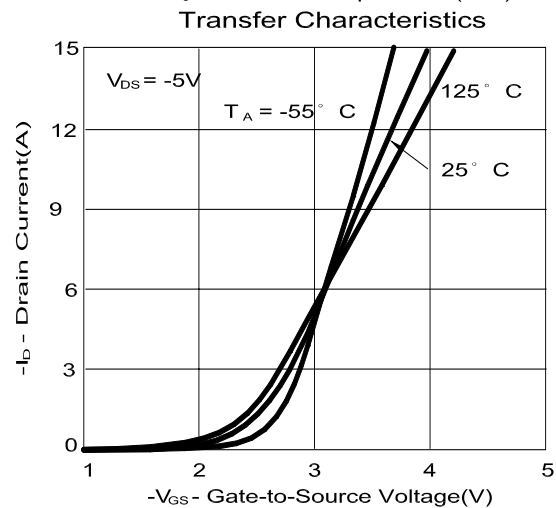
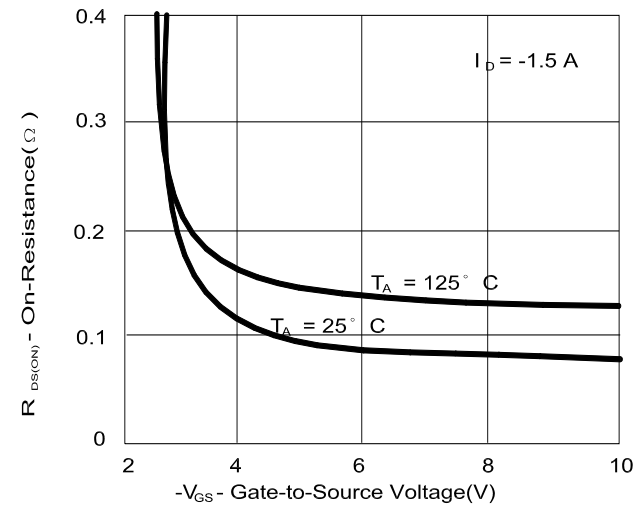
On-Resistance Variation with Drain Current and Gate Voltage



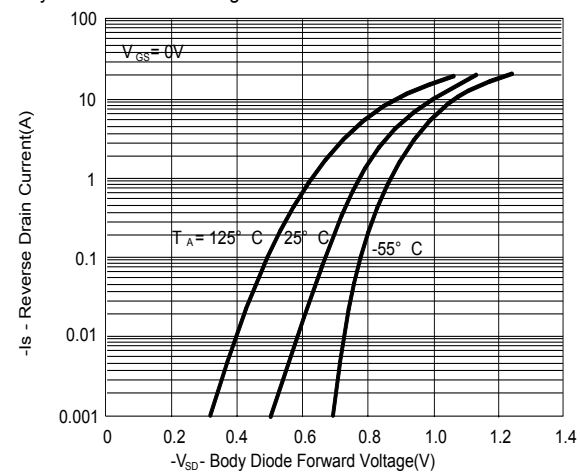
On-Resistance Variation with Temperature



On-Resistance Variation with Gate-to-Source Voltage



Body Diode Forward Voltage Variation with Source Current and Temperature



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